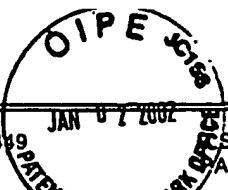
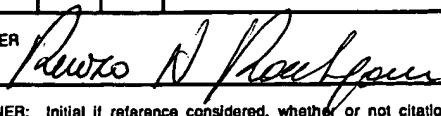


Form PTO-1449			U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1668	SERIAL NO. 09/943,190	
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						FILING DATE August 29, 2001	GROUP 2818, 2825	
U. S. PATENT DOCUMENTS								
Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date if Appropriate
	AA							
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	AL							
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	AN							
	AO							
	AP							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
PAR	AR	D.B. Johnson, et al., "Lateral Diffusion in Ag-Se Thin-Film Couples", Journal of Applied Physics, Vol. 40, No. 1, January 1969, pp. 149-152.						
	AS							
	AT							
EXAMINER <i>Phuoco N Phamgani</i>			DATE CONSIDERED <i>10/22/2004</i>					
<small>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>								

 Form PTO-1469 JAN 8 7 2002 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE LIST OF TRADEMARKS CITED BY APPLICANT (Use several sheets if necessary)					ATTY. DOCKET NO. MI22-1668	SERIAL NO. 09/943,190	
					APPLICANT Kristy A. Campbell	FEC-IV-2	
					FILING DATE August 29, 2001	GROUP 2846 72-825	
U.S. PATENT DOCUMENTS							
*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
	AA	08/797,635		Moore	—	—	03/01/2001
	AB	09/732,968		Gilton	—	—	12/08/2000
	AC	09/943,199		Campbell, et al.	—	—	08/29/2001
	AD	09/943,187		Campbell, et al.	—	—	08/29/2001
	AE	09/779,983		Moore	—	—	02/08/2001
	AF	5,238,882	08/24/93	Blalock et al.	—	—	
	AG	5,380,981	11/01/94	Owen et al.	—	—	
	AH	5,781,115	06/02/98	Kozicki et al.	—	—	
	AI	5,896,312	04/20/99	Kozicki et al.	—	—	
	AJ	5,914,693	06/22/99	Kozicki et al.	—	—	
	AK	6,084,796	07/04/00	Kozicki et al.	—	—	
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							Yes
	AL						No
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
	AR			Hirose, et al., "High Speed Memory Behavior and Reliability of an Amorphous As ₂ S ₃ Film Doped with Ag", July 17, 1980, pps. K187-K190.			
	AS			Hirose, et al., "Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As ₂ S ₃ films", Journal of Applied Physics, Vol. 47, No. 6, June, 1976, pps. 2767-2772.			
	AT			Kawaguchi, et al., "Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photoinduced and thermally induced phenomena of both systems", Journal of Applied Physics, 70, June 1996, pps. 9096-9104.			
EXAMINER				DATE CONSIDERED 10/22/2004			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. MI22-1668	SERIAL NO. 09/543,190
		LIST OF TRADEMARKS (use several sheets if necessary)		APPLICANT Kristy A. Campbell	RECEIVED GROUP 2825 2001-08-29
				FILING DATE August 29, 2001	

U.S. PATENT DOCUMENTS

TECHNICAL FIELD

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*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)

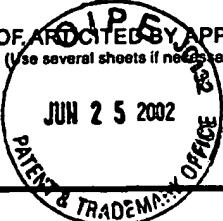
PAN	AR	Kluge, et al., "Silver photodiffusion in amorphous Ge _x Se _{100-x} ", Journal of Non-Crystalline Solids 124 (1990) pps. 188-193.
PAN	AS	Kolobov, A.V., "Photodoping of amorphous chalcogenides by metals", Advances in Physics, 1991, Vol. 40, No. 5, pps. 625-684.
PAN	AT	Mitkova, et al. "Dual Chemical Role of Ag as an Additive in Chalcogenide Glasses", Physical Review Letters, Vo. 83, No. 19, pps. 3848-3851.

EXAMINER	Pewro N. Radhyousi	DATE CONSIDERED	10/22/2004
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<p>Form PTO-1449 JAN 02 2002 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE</p> <p>PATENT & TRADEMARK OFFICE LAW OF ARTS LAW SHEETS IF NECESSARY</p>					ATTY. DOCKET NO. MI22-1668	SERIAL NO. 09/943,190
					APPLICANT Kristy A. Campbell	RECEIVED GROUP 2810-2825
					FILING DATE August 29, 2001	
U.S. PATENT DOCUMENTS						
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AM						No
AN						
AO						
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)						
PAR	AR	Mitrova, "Insulating and Semiconducting Glasses", Editor: P. Bockland, World Scientific, New Jersey, 2000, pp. 813-843.				
PAR	AS	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: Programmable Metallization Cell (PMC), (pre-July 7, 2000) pp. 1-6.				
PAR	AT	Shimakawa et al., Photoinduced effects and metastability in amorphous semiconductors and insulators, 44 ADVANCES IN PHYSICS No. 6, 475-588 (Taylor & Francis Ltd. 1995)				
EXAMINER	Patricia N. Roseman		DATE CONSIDERED		10/22/2004	
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>						

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 LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT: Kristy A. Campbell et al.			
					FILING DATE August 29, 2001		GROUP 2818 2825	
					U.S. PATENT DOCUMENTS			
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
<i>PAUL</i>	AA	09/921,518		Moore (as filed and as amended)			08/01/2001	
	AB	09/999,883		Moore (as filed)			03/01/2001	
	AC	10/061,825		Gilton et al. (as filed)			01/31/2002	
	AD	4,405,710	09/20/83	Balasubramanyam et al.	430	311		
	AE	4,419,421	12/06/83	Wichelhaus et al.	429	191		
	AF	4,499,557	02/12/85	Holmberg et al.	365	163		
	AG	5,315,131	05/24/94	Kishimoto et al.	257	57		
	AH	5,350,484	09/27/94	Gardner et al.	156	628		
	AI	5,512,328	04/30/96	Yoshimura et al.	427	498		
	AJ	5,512,773	04/30/96	Wolf et al.	257	471		
<i>PAUL</i>	AK	5,846,889	12/08/98	Harbison et al.	401	40		
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<i>PAUL</i>	AL	56126916 A	04.10.81	Abstract: Japan (Akira et al.)			X	
<i>PAUL</i>	AM	02/21542 A1	14.03.02	WIPO (Kozicki et al.)				
<i>PAUL</i>	AN	00/48196 A1	17.08.00	WIPO (Kozicki et al.)				
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EXAMINER	<i>Paul N. Harbison</i>			DATE CONSIDERED		<i>10/22/2004</i>		
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		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT: Kristy A. Campbell et al.			
					FILING DATE August 29, 2001		GROUP 2825	
U.S. PATENT DOCUMENTS								
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PAR	AA	6,117,720	09/12/00	Harshfield		438	238	
PAR	AB	6,143,604	11/07/00	Chiang et al.		438	253	
PAR	AC	6,177,338 B1	01/23/01	Liaw et al.		438	629	
PAR	AD	6,350,679 B1	02/26/02	McDaniel et al.		438	634	
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EXAMINER <i>Dewra N. Pantyani</i>		DATE CONSIDERED <i>10/22/2001</i>						
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**SUPPLEMENTAL INFORMATION
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STATEMENT BY APPLICANT**

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Sheet	1	of	8	Attorney Docket Number	M4065.0698/P698
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Complete If Known

Application Number	09/943,190
Filing Date	August 29, 2001
First Named Inventor	Kristy A. Campbell
Art Unit	2818 2823
Examiner Name	Not Yet Assigned

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
PA	AA	US 2002/0168820	11/14/2002	Kozicki et al.	
PA	AB	6,469,364	10/22/2002	Kozicki	
PA	AC	6,388,324	05/14/2002	Kozicki et al.	
PA	AD	US 2002/0000666	01/03/2002	Kozicki et al.	
PA	AE	5,500,532	03/19/1996	Kozicki et al.	
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
PA	BA	WO 97/48032	12/18/1997	Kozicki et al.		
PA	BB	WO 99/28914	06/10/1999	Kozicki et al.		
	BC					
	BD					

Examiner Signature	<i>Patricia N. Radtke</i>	Date Considered	10/22/2004
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¹Applicant's unique citation designation number (optional). ²See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 601.04. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

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Sheet

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Complete If Known

Application Number	09/943,190
Filing Date	August 29, 2001
First Named Inventor	Kristy A. Campbell
Group Art Unit	2818 2425
Examiner Name	Not Yet Assigned

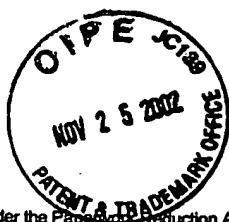
Attorney Docket Number M4065.0698/P698

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
DMR	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge5As38Te57 chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se75Ge25-xSbx, Appl. Phys. A 55 (1992) 167-169.	
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	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag2Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
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	CQ	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
	CR	Bernede, J.C., Switching and silver movements in Ag2Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
	CS	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.	
	CT	Bernede, J.C.; Conan, A.; Fousenant, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag2Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.	
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**SUPPLEMENTAL INFORMATION
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Application Number 09/943,190

Filing Date August 29, 2001

First Named Inventor Kristy A. Campbell

Group Art Unit 2818 7825

Examiner Name Not Yet Assigned

Attorney Docket Number M4065.0698/P698

PMR	Glasses, Asian Journal of Physics (2000) 9, 709-72.		
CX	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.		
CY	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703		
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CA1	Boolchand, P.; Enzweiler, R.N.; Tenhoven, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.		
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CN1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.		
CO1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.		
CP1	Dalven, R.; Gill, R., Electrical properties of beta-Ag2Te and beta-Ag2Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.		
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CR1	Dearmaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.		
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CT1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.		
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Reena N. Patel, P.E. 10/22/2009



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<i>PNR</i>	silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, <i>J. Non-Cryst. Solids</i> 198-200 (1996) 829-832.	
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SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	09/943,190
Sheet	5	of	8	Filing Date	August 29, 2001
				First Named Inventor	Kristy A. Campbell
				Group Art Unit	2818 7825
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0698/P698

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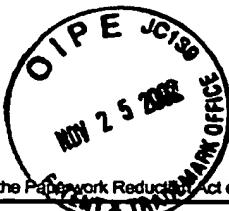
Application Number	09/943,190
Filing Date	August 29, 2001
First Named Inventor	Kristy A. Campbell
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Examiner Name	Not Yet Assigned

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	CY3	Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.
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<p><i>Par</i></p>	CM4	Owen, A.E.; Firth, A.P.; Ewen, P.J.S., Photo-induced structural and physico-chemical changes in amorphous chalcogenide semiconductors, <i>Phil. Mag. B</i> 52 (1985) 347-362.	
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First Named Inventor	Kristy A. Campbell
Group Art Unit	2818 2925
Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0698/P698

CK5	Thornburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, <i>Journal(??)</i> (1972) 4609-4612.
CL5	Tichy, L.; Ticha, H., Remark on the glass-forming ability in GexSe1-x and AsxSe1-x systems, <i>J. Non-Cryst. Solids</i> 261 (2000) 277-281.
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CD5	
CX5	
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Examiner Signature	<i>Revolv/Markjones</i>	Date Considered	10/22/2004
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Group Art Unit	2825	
Examiner Name	R. Rocchegiani	
Attorney Docket Number	M4065.0698/P698	

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U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
AR	AA	2002/0072188	6/13/2002	Gilton	
	AB	2002/0106849	08/08/2002	Moore	
	AC	2002/0123169	09/05/2002	Moore et al.	
	AD	2002/0123248	09/05/2002	Moore et al.	
	AE	2002/0160551	10/31/2002	Harshfield	
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	AK	2003/0045054	03/06/2003	Campbell et al.	
	AL	2003/0047765	03/13/2003	Campbell	
	AM	2003/0047772	03/13/2003	Li	
	AN	2003/0047773	03/13/2003	Li	
	AO	2003/0048519	03/13/2003	Kozicki	
	AP	2003/0068861	04/10/2003	Li	
	AQ	2003/0068862	04/10/2003	Li	
	AR	2003/0095426	05/22/2003	Hush et al.	
	AS	2003/0096497	05/22/2003	Moore et al.	
	AT	2003/0107105	06/12/2003	Kozicki	
	AU	2003/0117831	06/26/2003	Hush	
	AV	2003/0128612	07/10/2003	Moore et al.	
	AW	2003/0137869	07/24/2003	Kozicki	
	AX	2003/0143782	07/31/2003	Gilton et al.	
	AY	2003/0155589	08/21/2003	Campbell et al.	
	AZ	2003/0155606	08/21/2003	Campbell et al.	
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	AF1	3,622,319	11/1971	Sharp	
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	AH1	4,269,935	5/1981	Masters et al.	
	AI1	4,312,938	1/1982	Drexler, et al.	
	AJ1	4,316,946	1/1982	Masters, et al.	
	AK1	4,320,191	3/1982	Yoshikawa et al.	
	AL1	4,405,710	9/1983	Balasubramanyam et al.	
	AM1	4,419,421	12/1983	Wichelhaus, et al.	
	AN1	4,499,557	2/1985	Holmberg et al.	
	AO1	4,671,618	06/09/1987	Wu et al.	
	AP1	4,795,657	1/1989	Formigoni et al.	
	AQ1	4,800,526	01/24/1989	Lewis	
	AR1	4,847,674	7/1989	Sliwa et al.	
	AS1	5,177,567	1/1993	Klersy et al.	

Reiko Rocchegiani 10/22/2004

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Application Number	09/943,190
Filing Date	August 29, 2001
First Named Inventor	Kristy A. Campbell
Group Art Unit	2825
Examiner Name	R. Rocchegiani

Attorney Docket Number M4065.0698/P698

AT1	5,219,788	6/1993	Abernathay et al.
AU1	5,238,862	8/1993	Blalock et al.
AV1	5,272,359	12/21/1993	Nagasubramanian et al.
AW1	5,314,772	5/24/1994	Kozicki
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AY1	5,350,484	9/1994	Gardner et al.
AZ1	5,360,981	11/1994	Owen et al.
AA2	5,500,532	3/19/1996	Kozicki et al.
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AF3	6,423,628	7/2002	Li et al.
AG3	6,469,364	10/2002	Kozicki
AH3	6,473,332	10/2002	Ignatiev et al.
AI3	6,487,106	11/26/2002	Kozicki
** AJ3	2004/0038480	02/2004	Moore et al.
** AK3	2004/0042259	03/2004	Campbell et al.
** AL3	2004/0053461	03/2004	Moore et al.
** AM3	4,115,872	09/1978	Bluhm
** AN3	4,177,475	12/1979	Holmberg
** AO3	4,203,123	05/1980	Shanks
** AP3	4,653,024	03/1987	Young et al.
** AQ3	5,363,329	11/1994	Troyan


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Filing Date	August 29, 2001
First Named Inventor	Kristy A. Campbell
Group Art Unit	2825
Examiner Name	R. Rocchegiani
Attorney Docket Number	M4065.0698/P698

FOREIGN PATENT DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Foreign Patent Document Country Code ³ Number ⁴ Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²

Examiner Signature

Ricardo N. Rocchegiani

Date Considered

10/22/2004

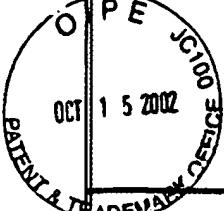
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			APPLICANT: Kristy A. Campbell et al.					
			FILING DATE August 29, 2001		GROUP 2818-2825			
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MAS	AA	3,622,319	11/23/71	Sharp		96	27	
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	AF	4,795,657	01/03/89	Formigoni et al.		427	96	
	AG	4,847,674	07/11/89	Silwa et al.		357	67	
	AH	5,177,567	01/05/93	Klersy et al.		257	4	
	AI	5,219,788	06/15/93	Abernathey et al.		437	187	
	AJ	5,726,083	03/10/98	Takaishi		438	210	
MAS	AK	5,751,012	05/12/98	Wolstenholme et al.		257	5	
FOREIGN PATENT DOCUMENTS								
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	AM							No
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
MAS	AN	Das et al., <i>Theory of the characteristic curves of the silver chalcogenide glass inorganic photoresists</i> , 54 APPL. PHYS. LETT., No. 18, pp. 1745-1747 (May 1989).						
		/ Helbert et al., <i>Intralevel hybrid resist process with submicron capability</i> , SPIE Vol. 333						
MAS	AO	/ <i>SUBMICRON LITHOGRAPHY</i> pp. 24-29 (1982)						
		Hill, DISSERTATION: <i>Materials Characterization of Silver Chalcogenide Programmable Metallization Cells</i> , Arizona State University, pp. title page-114 (UMI Company, May 1999).						
EXAMINER <i>M. D. S.</i>			DATE CONSIDERED 10/31/04					
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U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
MI22-1668SERIAL NO.
09/943,190LIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)

APPLICANT: Kristy A. Campbell et al.

FILING DATE
August 29, 2001GROUP
2818 2825

U.S. PATENT DOCUMENTS

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mn	AA	5,789,277	08/04/98	Zahorik et al.	438	95	
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	AF	6,236,059 B1	05/22/01	Wolstenholme et al.	257	3	
	AG	6,297,170 B1	10/02/01	Gabriel et al.	438	738	
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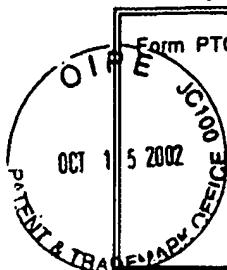
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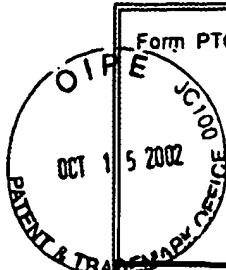
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		<i>10/31/02</i>

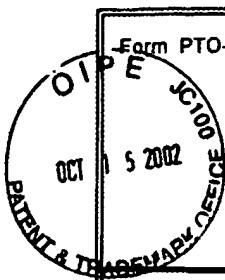
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					FILING DATE August 29, 2001		GROUP 2818 2825	
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ms	AA	6,376,284 B1	04/23/02	Gonzalez et al.		438	129	
	AB	6,391,688 B1	05/21/02	Gonzalez et al.		438	128	
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	AD	6,418,049 B1	07/09/02	Kozicki et al.		365	174	
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ms	AN	McHardy et al., <i>The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation</i> , 20 J. PHYS. C: SOLID STATE PHYS., pp. 4055-4075 (1987).						
ms	AO	Miyatani, <i>Electrical Properties of Ag₂Se</i> , 13 J. Phys. Soc. Japan, p. 317 (1958).						
ms	AP	Mizusaki et al. <i>Kinetic Studies on the Selenization of Silver</i> , 47 BUL. CHEM. SOC. JAPAN., No. 11 pp. 2851-2855 (November 1974).						
EXAMINER <i>Mark A. S.</i>			DATE CONSIDERED 8/31/04					
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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT: Kristy A. Campbell et al.					
			FILING DATE August 29, 2001		GROUP 2818 2825			
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MM	AA	10/077,867		Campbell et al. (as filed)				02/20/2002
MM	AB	10/232,757		Li, et al. (as filed)				08/29/2002
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
MM	AN	Owens et al., <i>Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures</i> , NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (Academic Press, 1989).						
MM	AO	Safran et al., <i>TEM study of Ag₂Se developed by the reaction of polycrystalline silver films and selenium</i> , 317 THIN SOLID FILMS, pp. 72-76 (1998).						
MM	AP	Shimizu et al., <i>The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses</i> , 46 BUL. CHEM. SOC. JAPAN, No. 12, pp. 3662-3665 (December 1973).						
EXAMINER <i>Mark J. Sul</i>				DATE CONSIDERED <i>10/31/04</i>				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.								



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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT: Kristy A. Campbell et al.	
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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m/s	AN	Somogyi et al., <i>Temperature Dependence of the Carrier Mobility in Ag_xSe Layers Grown on NaCl and SiO₂ Substrates</i> , 74 ACTA PHYSICA HUNGARICA, No. 3, pp. 243-255 (1994).					
		Tai et al., <i>Multilevel Ge-Se film based resist systems</i> , SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 32-39 (March 1982).					
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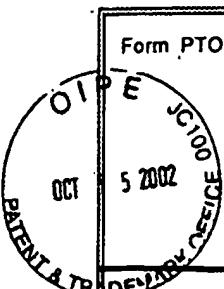
EXAMINER *Mark J. Lai*

DATE CONSIDERED

10/31/04

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		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1668		SERIAL NO. 09/943,190		
		LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			APPLICANT: Kristy A. Campbell et al.				
					FILING DATE August 29, 2001		GROUP 2010-2825		
U.S. PATENT DOCUMENTS									
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)									
<i>ms</i>	AN		West, DISSERTATION: <i>Electrically Erasable Non-Volatile Memory Via electrochemical Deposition of Multifractal Aggregates</i> , Arizona State University, pp. title page-168 (UMI Co., May 1998).						
<i>ms</i>	AO		West et al., <i>Equivalent Circuit Modeling of the Ag As_{0.24}S_{0.32}Ag_{0.40}Ag System Prepared by Photodissolution of Ag</i> , 145 J. Electrochem. Soc., No. 9, pp. 2971-2974 (September 1998).						
<i>ms</i>	AP		Yoshikawa et al., <i>A new inorganic electron resist of high contrast</i> , 31 APPL. PHYS. LETT., No. 3, pp. 161-163 (August 1977).						
EXAMINER <i>Mark S. Lee</i>				DATE CONSIDERED 10/31/07					

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			ATTY. DOCKET NO. MI22-1668		SERIAL NO. 09/943,190	
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		pp. 107-109 (January 1980).						
	AO							
	AP							
EXAMINER <i>Mark J. Savel</i>		DATE CONSIDERED <i>10/31/04</i>						
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